

Thermal Conductance Engineering for High-Speed TES Microcalorimeters

motivation, design, and initial characterization

James Hays-Wehle

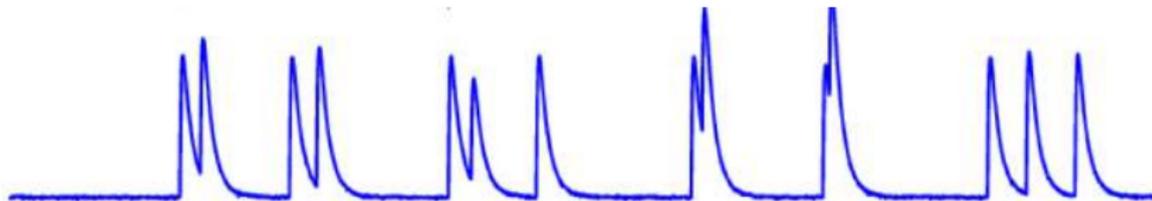
NIST: D. Schmidt, D. Swetz, and J. Ullom

LANL: M. Croce and M. Rabin

U MiB: A. Nucciotti

U Genoa: F. Gatti

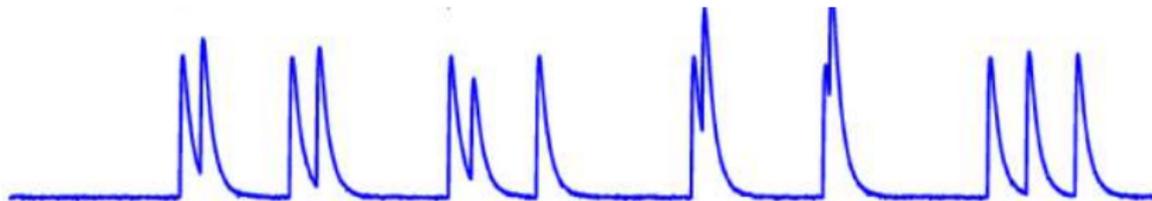
Need for Speed



Preventing Pile-up

- Need to match rep-rates at light sources
- 100 Kcps arrays planned

Need for Speed



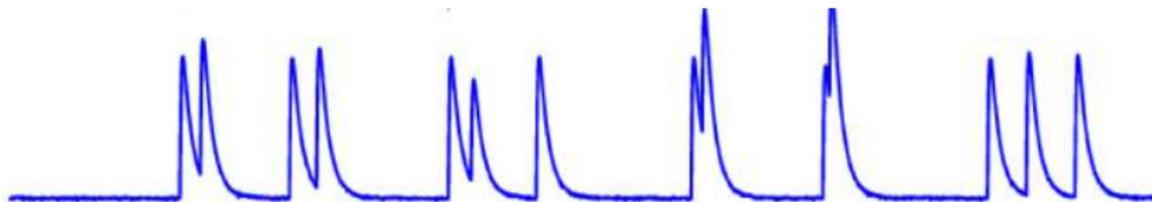
Preventing Pile-up

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Identifying Pile-up

- Coincident pulses that could distort spectra can be cut

Need for Speed



Preventing Pile-up

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Identifying Pile-up

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Now have the bandwidth to achieve this

- See J.A.B. Mates, J. D. Gard, *et al.* on Tuesday

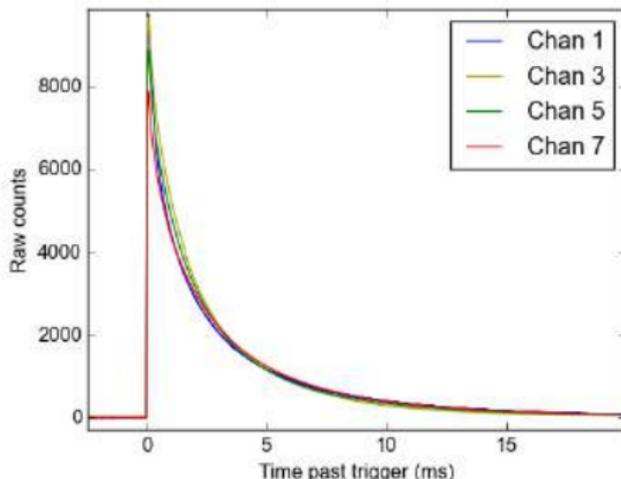
Constraints on Sensor Design

TES parameters

- C and α set by targeted energy range.
- $E_{\max} \propto C/\alpha$
- $\Delta E \propto \sqrt{4k_b T^2 C/\alpha}$
- Pulse speed chiefly determined by thermal conductance
- $\tau \propto C/G$

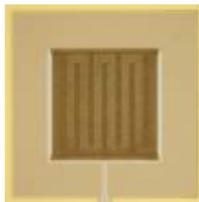
Goal

Increase G to improve pixel speed while maintaining resolution performance



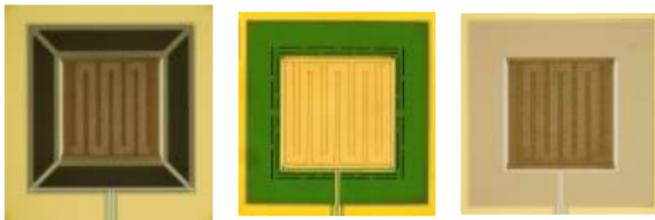
Current generation X-ray pulses. $\tau > 1$ ms

Historical control of G



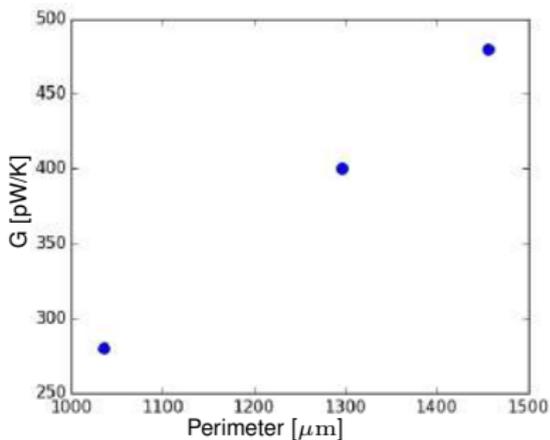
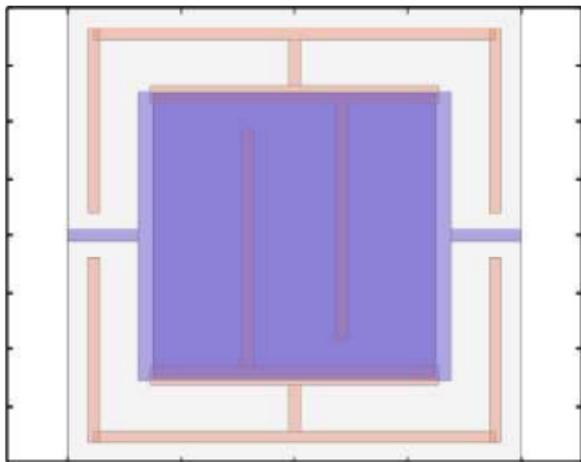
- TES thermally isolated on a SiN_x membrane.

Historical control of G



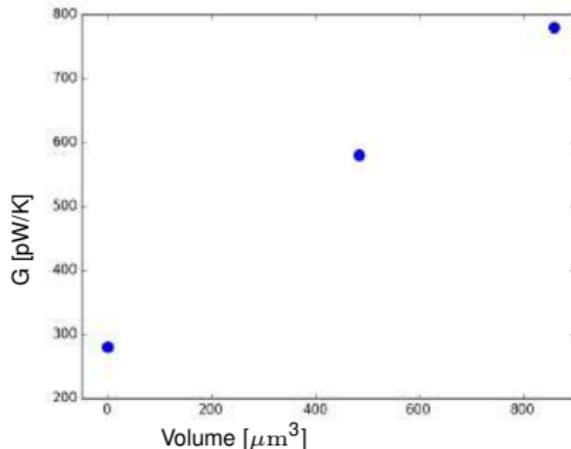
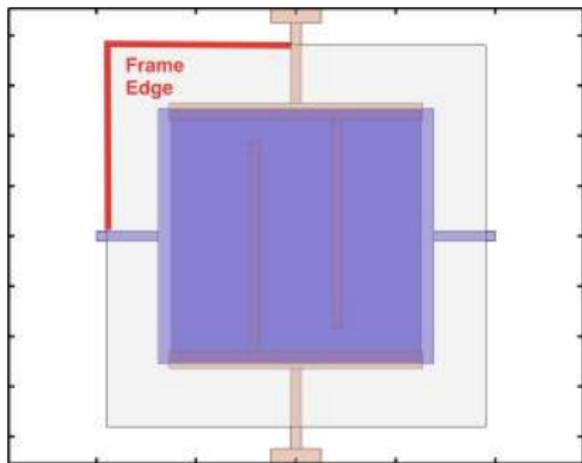
- TES thermally isolated on a SiN_x membrane.
- Perforated membranes used for *smaller* G to meet bandwidth constraints.
- Bare silicon G too much, fixed.

G increasing feature: perimeter



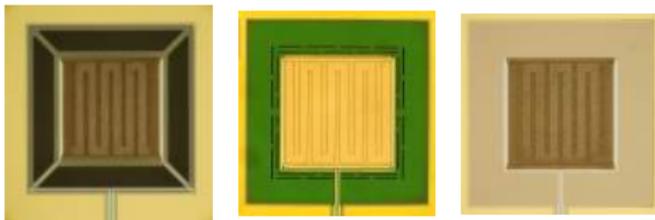
- On a membrane, G scales with perimeter.
 - Understood from 2-D ballistic phonon transport
- Test design doubles G relative to baseline device

G increasing feature: patches

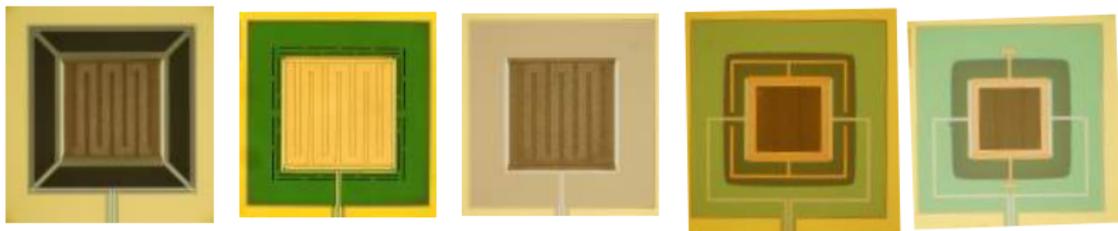


- Copper patches create thermal link directly to the frame
- Added G increases linearly with metal volume on frame
 - Understood from e-p coupling theory
- Test design trebles G of baseline device

Control of G



Control of G

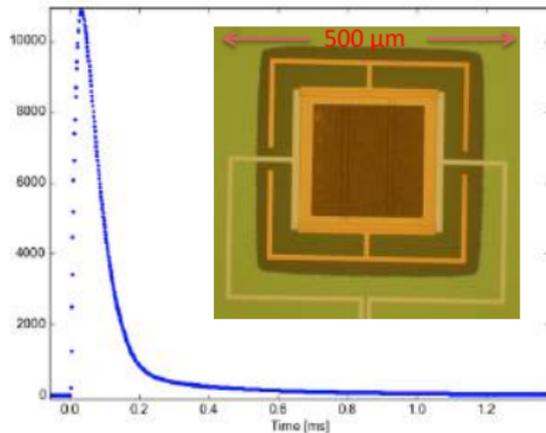
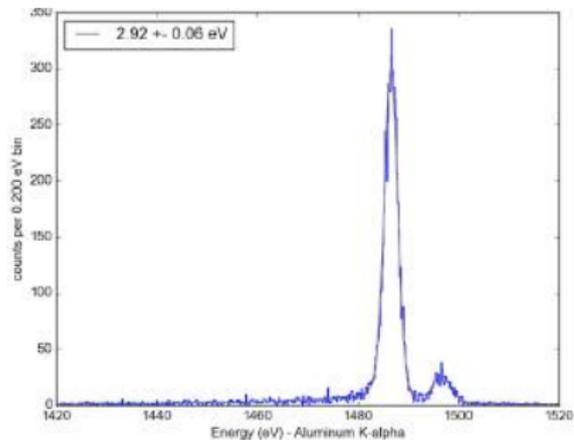


10 pW/K

1 nW/K

Predictable lithographic control of G over an order of magnitude.

Prototype Performance



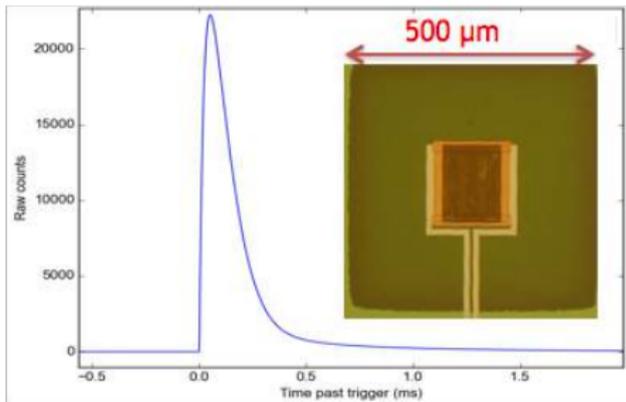
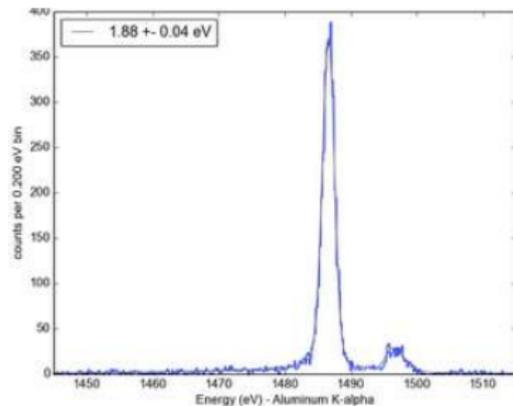
- $1/e$ fall time = $77 \mu\text{s}$
- Better than 3 eV FWHM resolution demonstrated at 1.5 keV
- Dynamic range up to 4 keV

Fin

- Detector speed greatly increased with lithographic features
- Performance maintained
- See poster for details

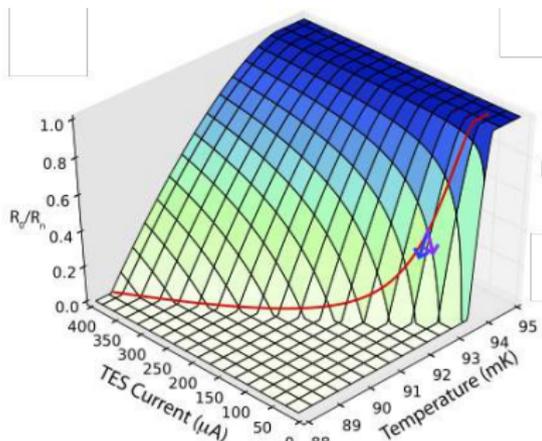
Thank You!

Another Prototype Performance



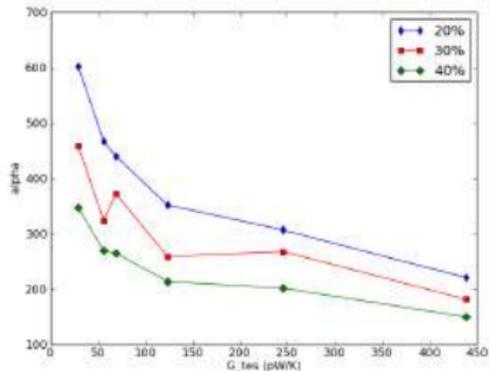
- 1/e fall time = 140 μs
- Better than 2eV FWHM resolution demonstrated at 1.5 keV
- Optimized for range up to 1 keV

Bonus Challenge



$R(I, T)$ surface in the 2-fluid model.

D. Bennett et al DOI:10.1007/s10909-011-0431-4



Previous experiments show a decreasing trend of α with G .

The two fluid model predicts that α is inversely proportional to I/I_C . Increasing G means increasing the bias current, which in turn suppresses α . We are exploring devices with higher resistances and fewer bars to compensate for this effect.